

U.S.S.N. 10/606,823

Claim Amendments

Please amend claims 24-31, 34-38 as follows:

Please add new claim 39 as follows:

U.S.S.N. 10/606,823

Listing of Claims

Claims 1- 23(canceled)

24. (currently amended) A method comprising:

exposing a semiconductor wafer to a first mask part that is at least partially defective to form a defectively exposed portion; and,

exposing the ~~semiconductor wafer~~ defectively exposed portion to a second mask part corresponding to the first mask part and that is at least substantially free from defects or with defects at different locations, wherein said first mask part and said second mask part are on different photomasks.

25. (currently amended) The method of claim 24, further comprising exposing the ~~semiconductor wafer~~ defectively exposed portion to the second mask part a second time.

26. (currently amended) The method of claim 25, further comprising exposing the ~~semiconductor wafer~~ defectively exposed

U.S.S.N. 10/606,823

portion to the second mask part a third time.

27. (currently amended) The method of claim 24, further comprising exposing the ~~semiconductor wafer~~ defectively exposed portion to the second mask part one or more additional times.

28. (currently amended) The method of claim 24 further comprising exposing the ~~semiconductor wafer~~ defectively exposed portion to the second, a third and other additional mask parts one or more additional times.

29. (currently amended) The method of claim 24, wherein the first mask part comprises a layout for a semiconductor device that is at least partially defective, and the second mask part comprises ~~[[a]]~~ the layout for the semiconductor device that is at least substantially free from defects or with defects at different locations.

30. (currently amended) The method of claim 24, wherein exposing the semiconductor wafer to the first mask part and exposing the ~~semiconductor wafer~~ defectively exposed portion to the second mask part ~~are part of~~ comprise a lithographic semiconductor fabrication process.

U.S.S.N. 10/606,823

31. (currently amended) A method comprising:

exposing a semiconductor wafer to a first mask part that comprises a layout for a semiconductor device that is at least partially defective to form a defectively exposed portion; and

exposing the ~~semiconductor wafer~~ defectively exposed portion to a second mask part corresponding to the first mask part that comprises [[a]] the layout for the semiconductor device that is at least substantially free from defects or with defects at different locations.

32. (previously presented) The method of claim 31, wherein the first mask part and the second mask part are on a same photomask.

33. (previously presented) The method of claim 31, wherein the first mask part and the second mask part are on different photomasks.

34. (currently amended) The method of claim 31, further comprising exposing the ~~semiconductor wafer~~ defectively exposed

U.S.S.N. 10/606,823

portion to the second mask part a second time.

35. (currently amended) The method of claim [[31]] 34, further comprising exposing the semiconductor wafer to the second mask part a third time.

36. (currently amended) The method of claim 31, further comprising exposing the ~~semiconductor wafer~~ defectively exposed portion to the second mask part one or more additional times:

37. (currently amended) The method of claim 31 further comprising exposing the ~~semiconductor wafer~~ defectively exposed portion to the second, a third and other additional mask parts one or more additional times.

38. (currently amended) The method of claim 31, wherein exposing the semiconductor wafer to the first mask part and exposing the ~~semiconductor wafer~~ defectively exposed portion to the second mask part ~~are part of~~ comprise a lithographic semiconductor fabrication process.

39. (new) A method for repairing a defectively exposed

U.S.S.N. 10/606,823

semiconductor wafer comprising:

exposing a semiconductor wafer to a first mask part that is at least partially defective to form a defectively exposed portion; and,

exposing the defectively exposed portion to a second mask part corresponding to the first mask part and that is at least substantially free from defects or with defects at different locations to at least partially repair said defectively exposed portion.